

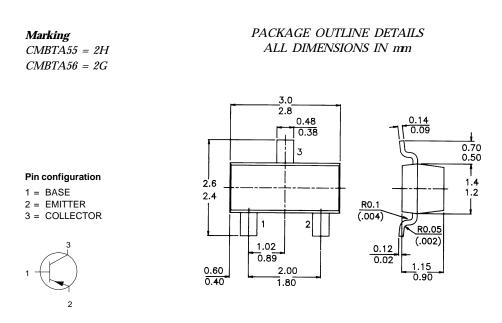


SOT-23 Formed SMD Package

CMBTA55 CMBTA56

SILICON EPITAXIAL TRANSISTORS

P-N-P transistor



ABSOLUTE MAXIMUM RATINGS

	CMBT A	4 <i>55</i>		A56	;
$-V_{CBO}$	max.	60		80	V
$-V_{CEO}$	max.	60		80	V
$-V_{EBO}$	max.		4	V	
$-I_C$	max.		500		mА
P _{tot}			250		mW
h_{FE}	min.		100		
f_T	min.		50		MHz
V _{CEsat}	max.		0.25		V
	$-V_{CEO}$ $-V_{EBO}$ $-I_C$ P_{tot} h_{FE} f_T	$-V_{CBO}$ max. $-V_{CEO}$ max. $-V_{EBO}$ max. $-I_C$ max. P_{tot} min. h_{FE} min. f_T min.	$\begin{array}{cccc} -V_{CEO} & max. & \underline{60} \\ -V_{EBO} & max. \\ -I_C & max. \\ P_{tot} \\ h_{FE} & min. \\ f_T & min. \end{array}$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $

CMBTA55 CMBTA56

RATINGS (at $T_A = 25^{\circ}C$ unless otherwise specified) Limiting values

Liniting village					
		CMBTA55		A56	3
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	60	80	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	60	80	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.		4	V
Collector current (d.c.)	$-I_C$	max.		500	mА
Total power dissipation up to $T_{amb} = 25 \ ^{\circ}C$	P _{tot}	max.		250	mW
Storage temperature	Tstg		-55	5 to +150	° C
Junction temperature	T_j	max.		150	° C

THERMAL CHARACTERISTICS

$T_j = P (R_{th j-t} + R_{th t-s} + R_{th s-a}) + 2$	T _{amb}		
Thermal resistance			
from junction to ambient	R _{th j-a}	500	K/W

CHARACTERISTICS (at $T_A = 25^{\circ}C$ unless otherwise specified)

Collector-emitter breakdown voltage	CMBTA55			A56
$-I_C = 1 mA; I_B = 0$	$-V_{(BR)CE}$	0 min. 60		80 V
Emitter-base breakdown voltage				
$-I_C = 0; I_E = 100 \ \mu A$	$-V_{(BR)EB}$) min.	4	V
Collector cut-off current				
$-V_{CE} = 60 V; I_B = 0$	$-I_{CEO}$	max.	0.1	μA
$-V_{CB} = 60 V; I_E = 0$	-ICBO	max. 0.1		- μA
$-V_{CB} = 80 V; I_E = 0$	-I _{CBO}	max.		0.1 µA
Saturation voltages				
$-I_C = 100 \text{ mA}; -I_B = 10 \text{ mA}$	-VCEsat	max.	0.25	V
Base-emitter On voltage				
$-I_C = 100 \text{ mA}; -V_{CE} = 1 \text{ V}$	$-V_{BE(on)}$	max.	1.2	V
D.C. current gain				
$-I_C = 10 \ mA; \ -V_{CE} = 1 \ V$	h_{FE}	min.	100	
$-I_C = 100 \text{ mA}; -V_{CE} = 1 \text{ V}$	h_{FE}	min.	100	
Transition frequency at $f = 100 \text{ MHz}$				
$-I_C = 100 \text{ mA}; -V_{CE} = 1 \text{ V}$	f_T	min.	50	MHz

Customer Notes

Disclaimer

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Data Sheet

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